

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0011] with the following revised paragraph:

[0011] A four transistor (4T) SRAM uses a high value resistor as its load device. The attraction of 4T SRAM is the potential for reduced cell size compared to a 6T SRAM (which uses transistors instead for load devices). The primary function of the load resistor is to supply enough current to compensate for the junction leakage and maintain the charge in the node. Junction leakage current typically ranges from femtoampere to picoampere (10^{-15} to $\pm 10^{-12}$ amps) for Field Effect Transistors (FET's) fabricated under contamination free conditions, which is the minimum current required from the loaded (p1, p2) power supply V_{dd} . A typical maximum resistor value acceptable is in the range of 10^2 to 10^{15} ohms, assuming a V_{dd} of 3 to 5 volts. The value of the resistor, in turn, is affected by availability of material that has very high intrinsic resistance and the cell area available for resistor layout. In addition, the resistor material and process should be compatible with silicon manufacturing.